

Silicon PNP transistor epitaxial type
A5926

[Applications]

Power amplifier
 Power switching

[Feature]

Low collector saturation voltage $V_{CE(sat)} = -0.5V$ (Typ.) at $I_C = -2A$, $I_B = -0.2A$

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-32	V
Emitter-base voltage	VEBO	-5	V
Collector current	IC	-2	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-40	-	-	V	$I_C = -50\mu A$, $I_E = 0A$
Collector-emitter breakdown voltage	BVCEO	-32	-	-	V	$I_C = -1mA$, $I_B = 0A$
Emitter-base breakdown voltage	BVEBO	-5	-	-	V	$I_E = -50\mu A$, $I_C = 0A$
Collector cut-off current	ICBO	-	-	-1	μA	$V_{CB} = -20V$, $I_E = 0A$
Emitter cut-off current	IEBO	-	-	-1	μA	$V_{EB} = -4V$, $I_C = 0A$
DC current gain	hFE	82	-	390	-	$V_{CE} = -3V$, $I_C = -0.5A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-0.5	-0.8	V	$I_C = -2A$, $I_B = -200mA$
Transition frequency	fT	-	130	-	MHz	$V_{CE} = -5V$, $I_E = 0.5A$
Collector output capacitance	Cob	-	17	-	pF	$V_{CB} = -10V$, $f = 1MHz$, $I_E = 0A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

